

Vishay Siliconix

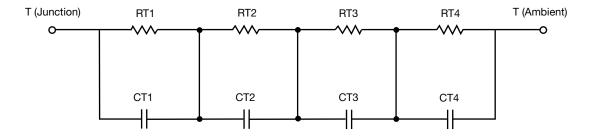
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
RT1	35.9996	213.9067m	N/A		
RT2	7.3518	449.6807m	N/A		
RT3	5.2672	246.2118m	N/A		
RT4	1.3708	190.2008m	N/A		
	THERMAL CAPACI	TANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	1.0816	4.0550m	N/A		
CT2	347.0692m	78.9844m	N/A		
CT3	37.5408m	297.0685m	N/A		
CT4	2.2136m	341.8020m	N/A		

Note

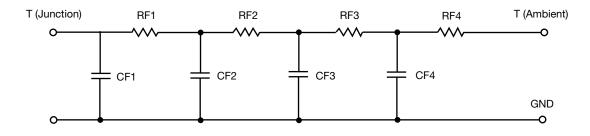
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	1.2716	260.8548m	N/A		
RF2	7.0101	702.2532m	N/A		
RF3	12.4348	109.0774m	N/A		
RF4	29.2241	27.8146m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	1.4748m	4.0642m	N/A		
CF2	29.3503m	55.2295m	N/A		
CF3	286.9358m	68.0395m	N/A		
CF4	1.0094	83.7224m	N/A		

Note

• n/a indicates not applicable

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